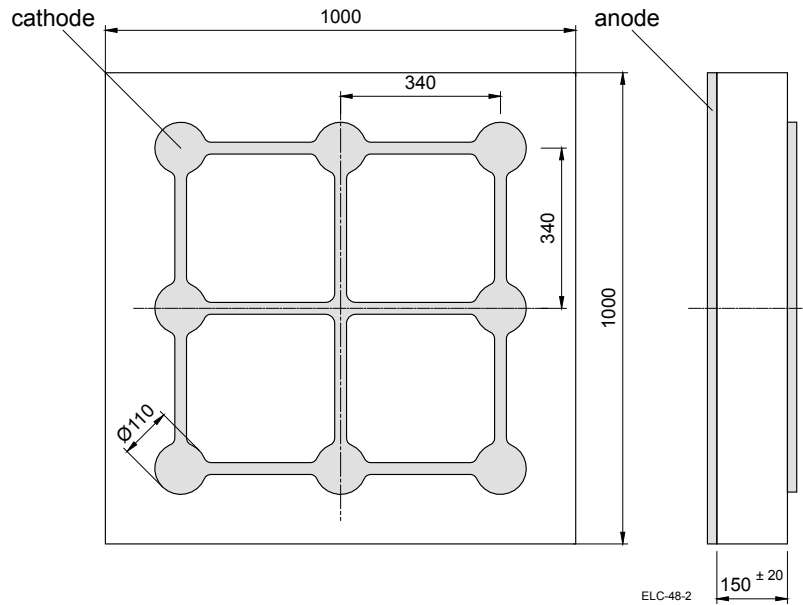


| Radiation | Type                    | Technology    | Electrodes     |
|-----------|-------------------------|---------------|----------------|
| Infrared  | Power chip, solder able | AlGaAs/GaAlAs | N (cathode) up |

**Outline** (dimensions in microns)



**Optical and Electrical Characteristics\***

T<sub>amb</sub> = 25°C, unless otherwise specified

| Parameter                 | Test conditions         | Symbol                          | Min | Typ | Max | Unit |
|---------------------------|-------------------------|---------------------------------|-----|-----|-----|------|
| Forward voltage           | I <sub>F</sub> = 300 mA | V <sub>F</sub>                  |     | 1.6 | 2.0 | V    |
| Reverse voltage           | I <sub>R</sub> = 10 µA  | V <sub>R</sub>                  | 5   |     |     | V    |
| Radiant power*            | I <sub>F</sub> = 300 mA | Φ <sub>e</sub>                  | 50  | 75  |     | mW   |
| Peak wavelength           | I <sub>F</sub> = 300 mA | λ <sub>p</sub>                  | 830 | 840 | 860 | nm   |
| Spectral bandwidth at 50% | I <sub>F</sub> = 300 mA | Δλ <sub>0.5</sub>               |     | 45  |     | nm   |
| Switching time            | I <sub>F</sub> = 300 mA | t <sub>r</sub> , t <sub>f</sub> |     | 40  |     | ns   |

\*Chip packaged on TO-46 header covered with epoxy, in cylindrical copper heatsink

**Labeling**

| Type         | Lot N° | Φ <sub>e</sub> (typ, min, max) | Quantity |
|--------------|--------|--------------------------------|----------|
| ELC-840-29-1 |        |                                |          |

**Packing:** Chips on adhesive film with wire-bond side on top